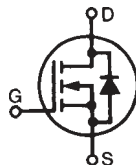


**TrenchT2™ GigaMOS™**  
**Power MOSFET**
**IXTK550N055T2**  
**IXTX550N055T2**

$$V_{DSS} = 55V$$

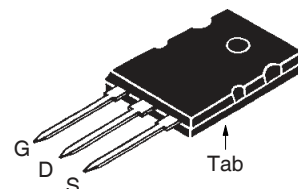
$$I_{D25} = 550A$$

$$R_{DS(on)} \leq 1.6m\Omega$$

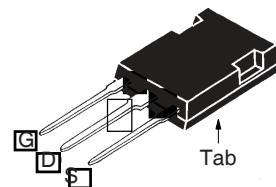
 N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	55	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	55	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$ (Chip Capability)	550	A
$I_{L(RMS)}$	External Lead Current Limit	160	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	1375	A
$I_A$	$T_C = 25^\circ C$	200	A
$E_{AS}$	$T_C = 25^\circ C$	3	J
$P_D$	$T_C = 25^\circ C$	1250	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

TO-264 (IXTK)



PLUS247 (IXTX)


 G = Gate      D = Drain  
 S = Source      Tab = Drain

**Features**

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters and Off-Line UPS
- Primary-Side Switch
- High Speed Power Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	55		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 150^\circ C$			10 $\mu A$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 100A$ , Notes 1 & 2			1.6 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	90	150	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		40	nF
$C_{oss}$			4970	pF
$C_{rss}$			1020	pF
$R_{GI}$	Gate Input Resistance		1.36	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 200\text{A}$ $R_G = 1\Omega$ (External)		45	ns
$t_r$			40	ns
$t_{d(off)}$			90	ns
$t_f$			230	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{DSS}$		595	nC
$Q_{gs}$			150	nC
$Q_{gd}$			163	nC
$R_{thJC}$				$0.12^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$			550 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			1700 A
$V_{SD}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.2 V
$t_{rr}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 27.5\text{V}$		100	ns
$I_{RM}$			5	A
$Q_{RM}$			250	nC

- Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .  
2. Includes lead resistance.

### ADVANCE TECHNICAL INFORMATION

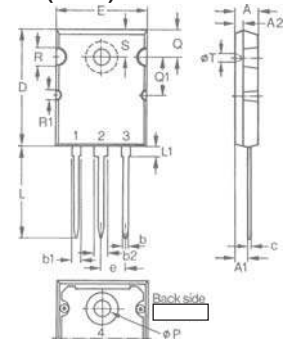
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

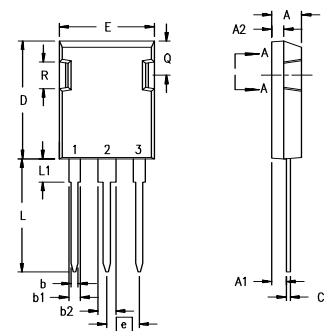
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

### TO-264 (IXTK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

### PLUS 247™ (IXTX) Outline



- Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

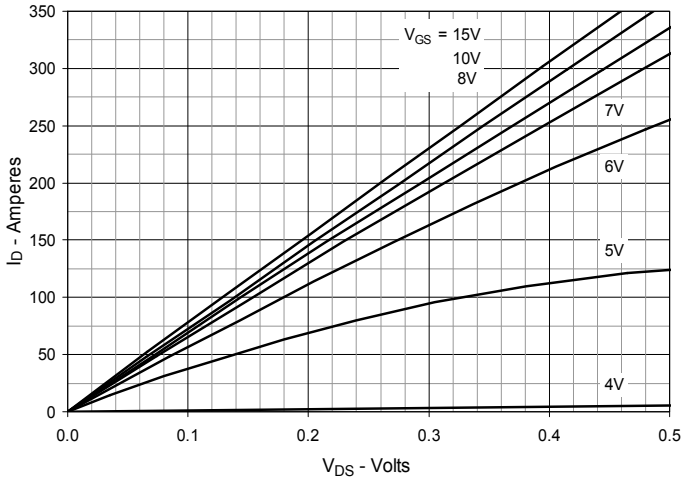


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

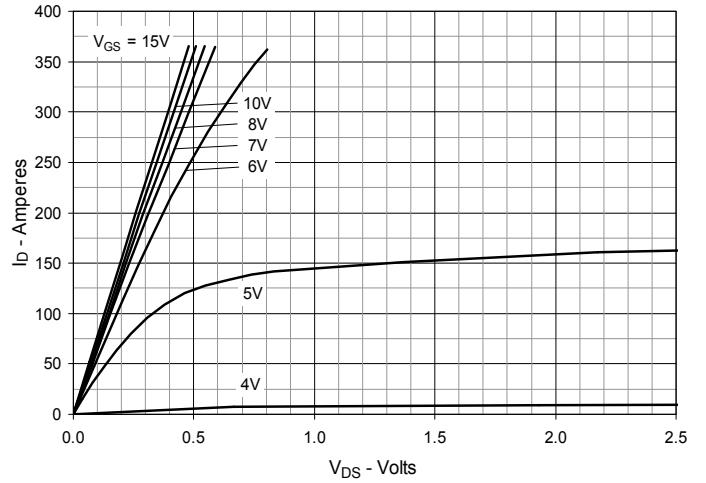


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

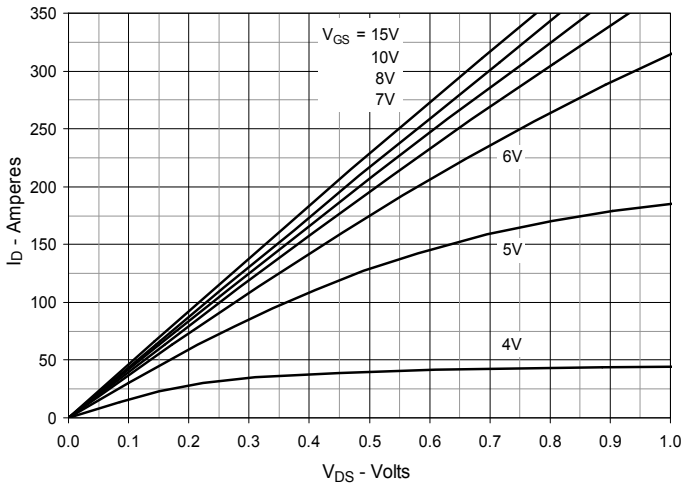


Fig. 4. Normalized  $R_{DS(on)}$  vs. Junction Temperature

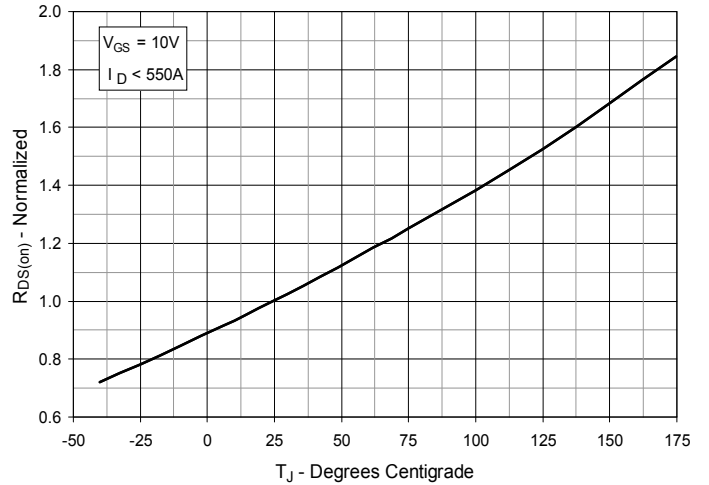


Fig. 5. Normalized  $R_{DS(on)}$  vs. Drain Current

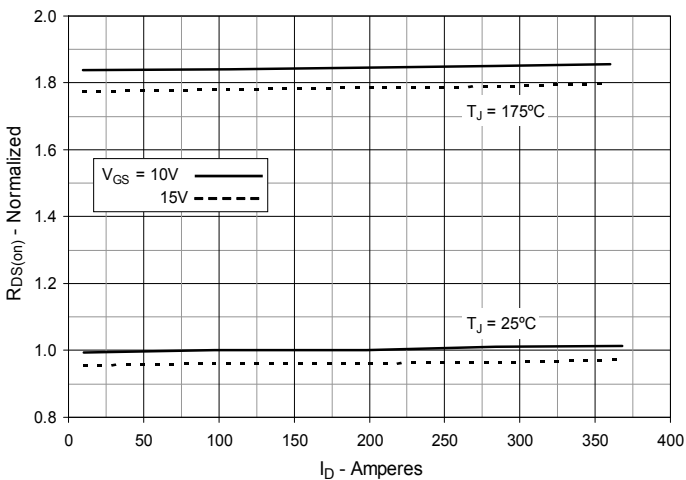
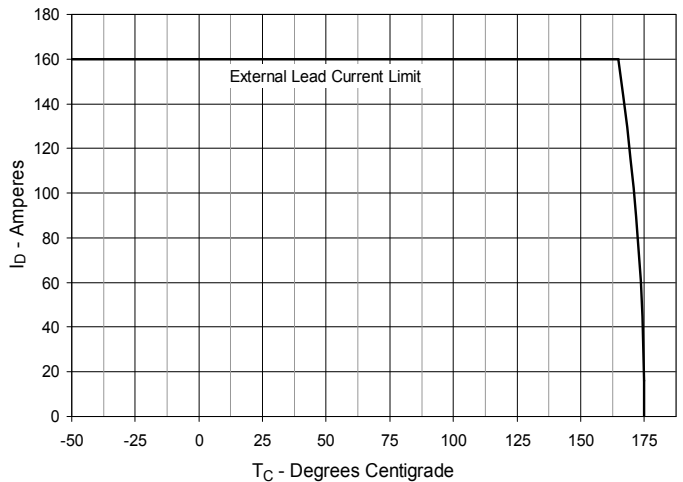
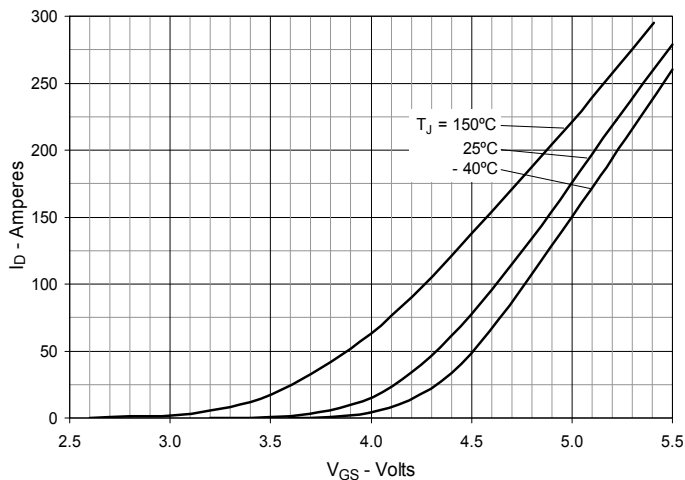


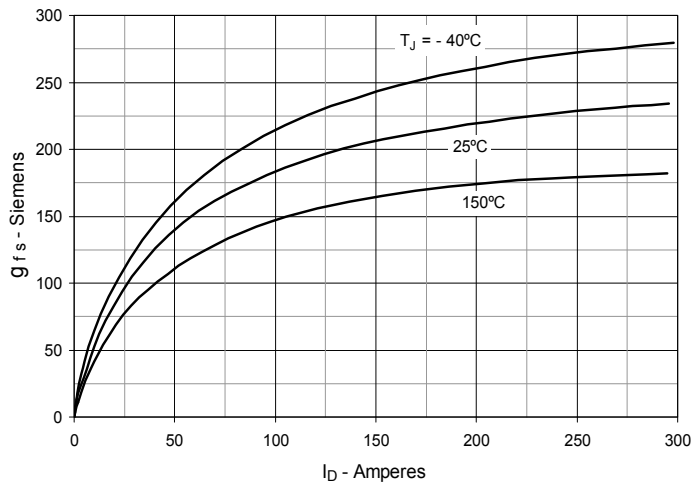
Fig. 6. Drain Current vs. Case Temperature



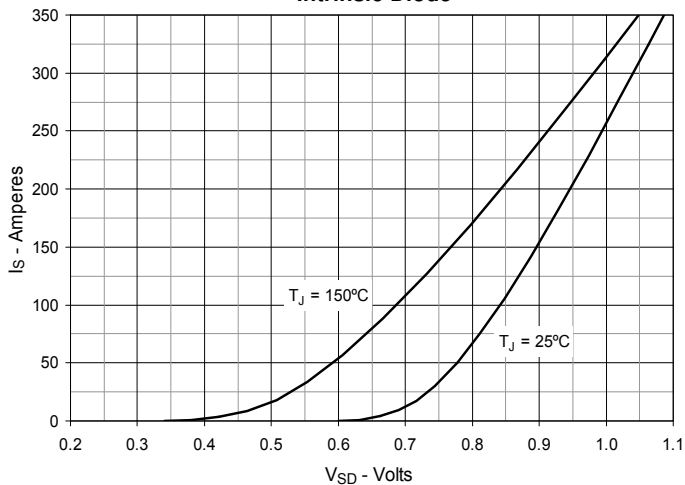
**Fig. 7. Input Admittance**



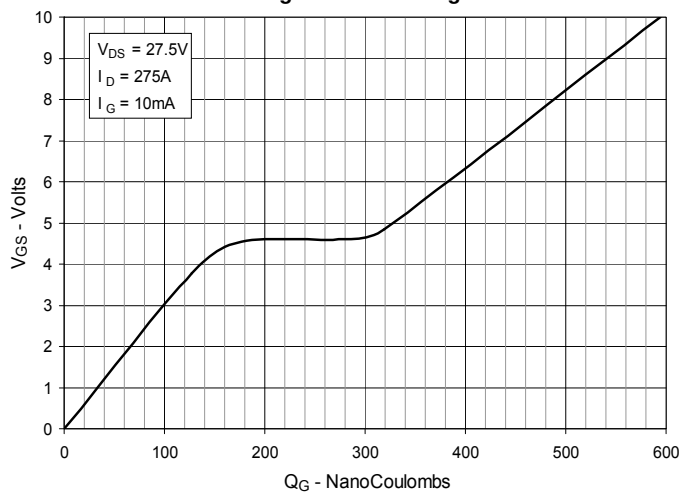
**Fig. 8. Transconductance**



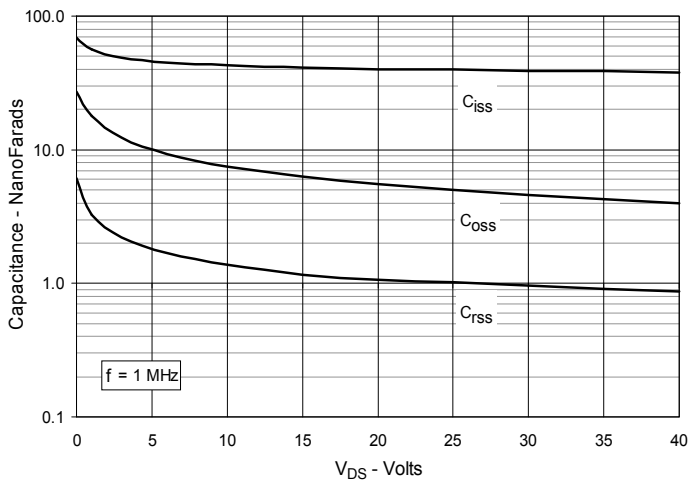
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



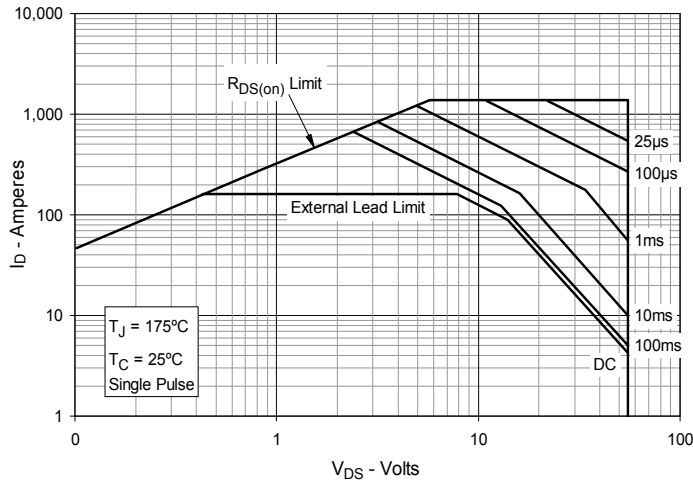
**Fig. 10. Gate Charge**



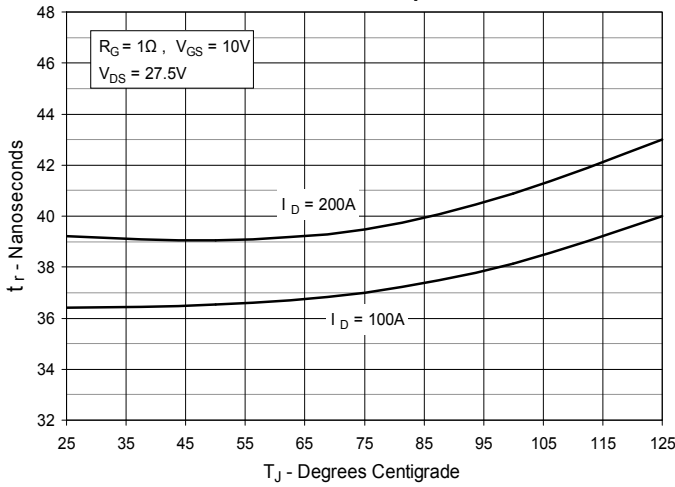
**Fig. 11. Capacitance**



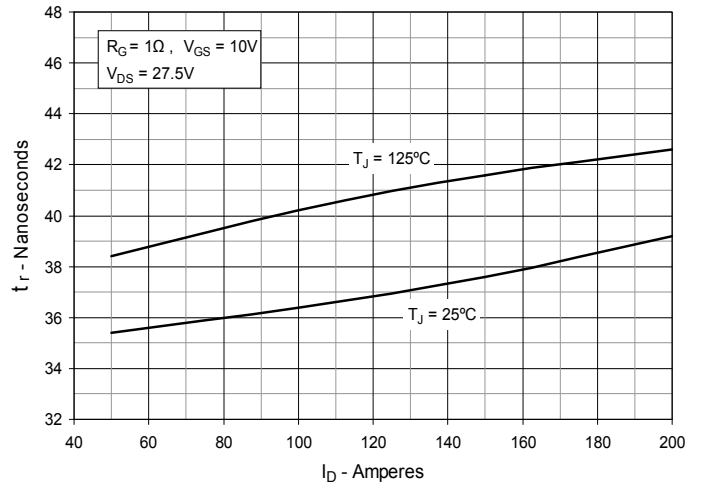
**Fig. 12. Forward-Bias Safe Operating Area**



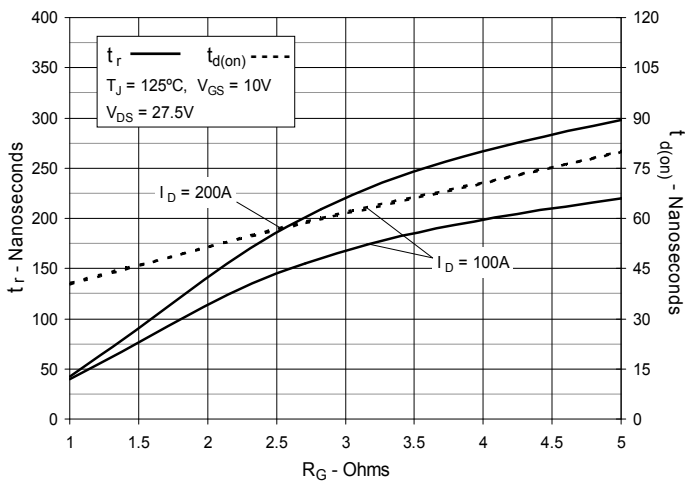
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



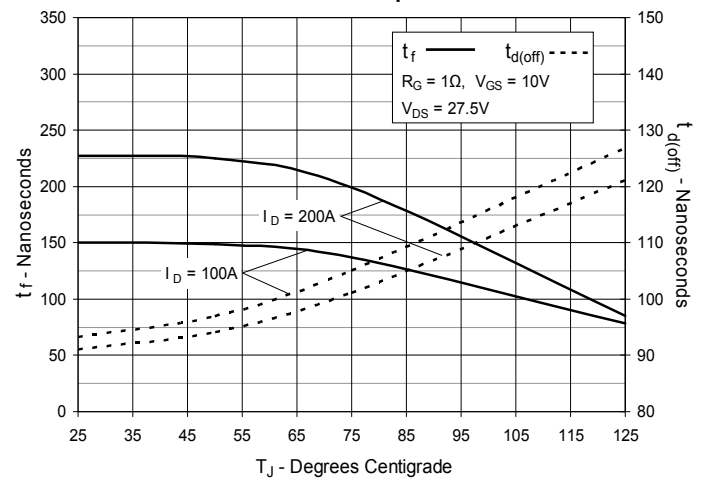
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



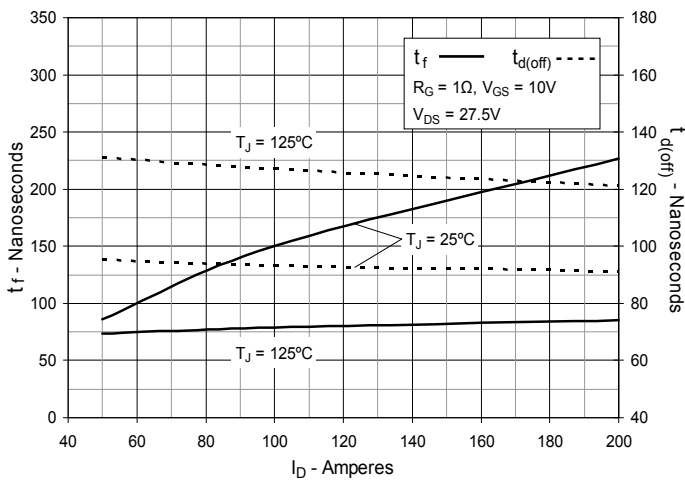
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

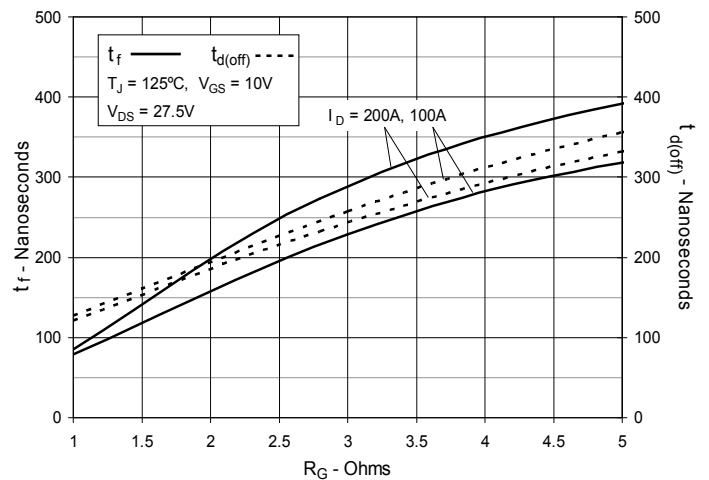
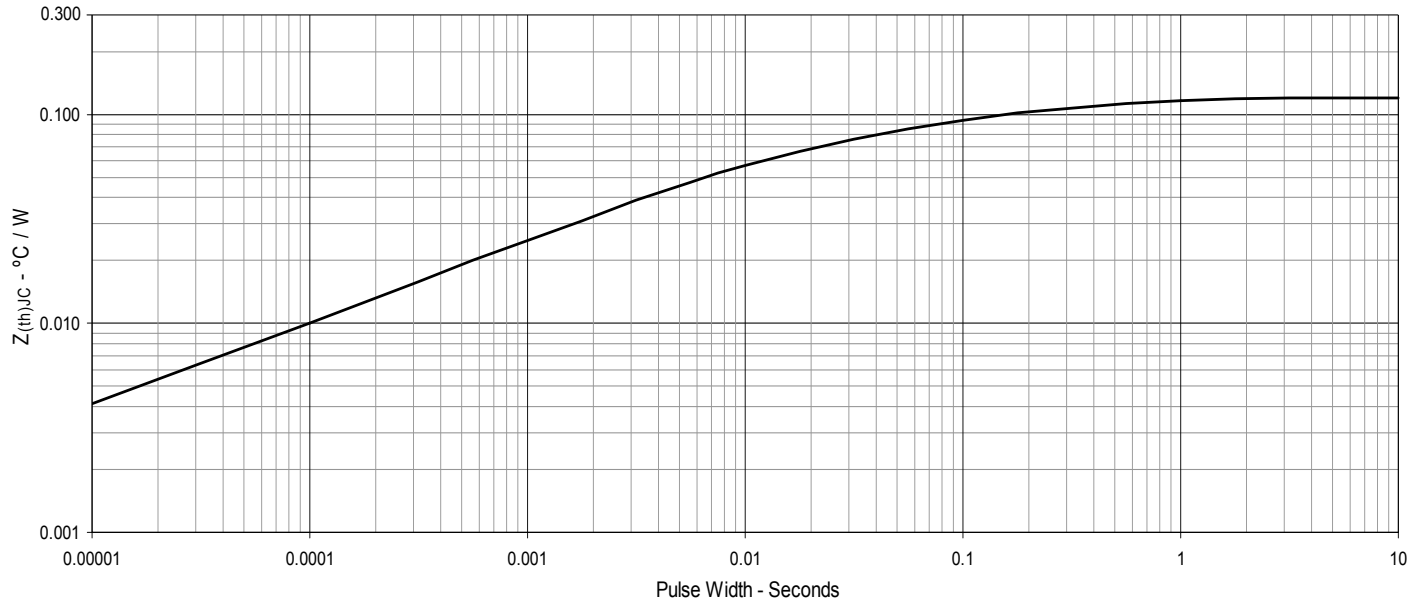


Fig. 19. Maximum Transient Thermal Impedance





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